



# STB95N3LLH6, STD95N3LLH6 STP95N3LLH6, STU95N3LLH6

N-channel 30 V, 0.0037  $\Omega$ , 80 A, D<sup>2</sup>PAK, DPAK, IPAK, TO-220  
STripFET™ VI DeepGATE™ Power MOSFET

## Features

Type	V <sub>DSS</sub>	R <sub>DS(on)</sub> max	I <sub>D</sub>
STB95N3LLH6	30 V	0.0042 $\Omega$	80 A
STD95N3LLH6	30 V	0.0042 $\Omega$	80 A
STP95N3LLH6	30 V	0.0042 $\Omega$	80 A
STU95N3LLH6	30 V	0.0047 $\Omega$	80 A

- R<sub>DS(on)</sub> \* Q<sub>g</sub> industry benchmark
- Extremely low on-resistance R<sub>DS(on)</sub>
- High avalanche ruggedness
- Low gate drive power losses

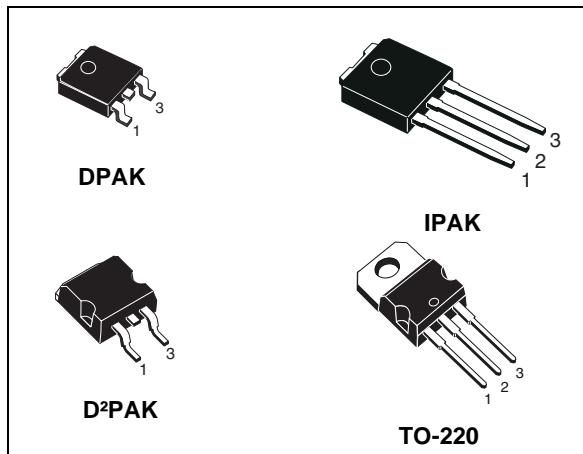
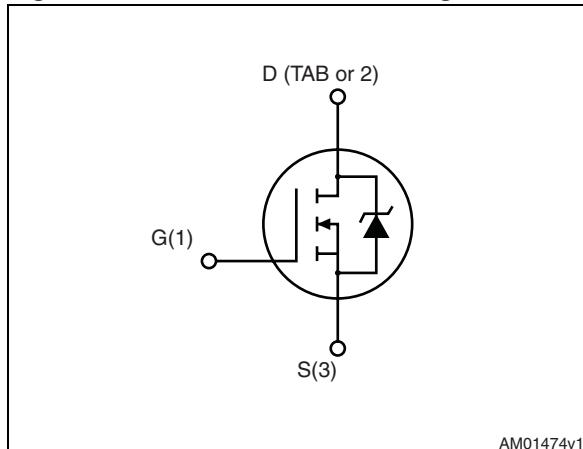


Figure 1. Internal schematic diagram



AM01474v1

Table 1. Device summary

Order codes	Marking	Package	Packaging
STB95N3LLH6	95N3LLH6	D <sup>2</sup> PAK	Tape and reel
STD95N3LLH6	95N3LLH6	DPAK	Tape and reel
STP95N3LLH6	95N3LLH6	TO-220	Tube
STU95N3LLH6	95N3LLH6	IPAK	Tube

## Contents

<b>1</b>	<b>Electrical ratings</b>	<b>3</b>
<b>2</b>	<b>Electrical characteristics</b>	<b>4</b>
2.1	Electrical characteristics (curves)	6
<b>3</b>	<b>Test circuits</b>	<b>8</b>
<b>4</b>	<b>Package mechanical data</b>	<b>10</b>
<b>5</b>	<b>Packaging mechanical data</b>	<b>16</b>
<b>6</b>	<b>Revision history</b>	<b>18</b>

# 1 Electrical ratings

**Table 2. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage ( $V_{GS} = 0$ )	30	V
$V_{GS}$	Gate-source voltage	$\pm 20$	V
$I_D^{(1)}$	Drain current (continuous) at $T_C = 25^\circ\text{C}$	80	A
$I_D$	Drain current (continuous) at $T_C = 100^\circ\text{C}$	61	A
$I_{DM}^{(2)}$	Drain current (pulsed)	320	A
$P_{TOT}$	Total dissipation at $T_C = 25^\circ\text{C}$	70	W
	Derating factor	0.47	W/ $^\circ\text{C}$
$E_{AS}^{(3)}$	Single pulse avalanche energy	150	mJ
$T_{stg}$	Storage temperature	-55 to 175	$^\circ\text{C}$
$T_j$	Max. operating junction temperature	175	$^\circ\text{C}$

1. Limited by wire bonding
2. Pulse width limited by safe operating area
3. Starting  $T_j = 25^\circ\text{C}$ ,  $I_{AV} = 55 \text{ A}$ ,  $L = 0.1 \text{ mH}$

**Table 3. Thermal data**

Symbol	Parameter	Value				Unit
		D <sup>2</sup> PAK	DPAK	IPAK	TO-220	
$R_{thj-case}$	Thermal resistance junction-case max	2.14		$^\circ\text{C/W}$		
$R_{thj-amb}$	Thermal resistance junction-ambient max		100		62.5	$^\circ\text{C/W}$
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb max	35	35			$^\circ\text{C/W}$
$T_I$	Maximum lead temperature for soldering purpose	275		300		$^\circ\text{C}$

1. When mounted on FR-4 board of 1 inch<sup>2</sup>, 2 oz Cu.

## 2 Electrical characteristics

( $T_{CASE} = 25^\circ\text{C}$  unless otherwise specified)

**Table 4. Static**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown Voltage	$I_D = 250 \mu\text{A}, V_{GS} = 0$	30			V
$I_{DSS}$	Zero gate voltage drain current ( $V_{GS} = 0$ )	$V_{DS} = 30 \text{ V}$ $V_{DS} = 30 \text{ V}, T_c = 125^\circ\text{C}$			1 10	$\mu\text{A}$ $\mu\text{A}$
$I_{GSS}$	Gate body leakage current ( $V_{DS} = 0$ )	$V_{GS} = \pm 20 \text{ V}$			$\pm 100$	nA
$V_{GS(\text{th})}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	1		2.5	V
$R_{DS(on)}$	Static drain-source on resistance	$V_{GS} = 10 \text{ V}, I_D = 40 \text{ A}$ SMD version		0.0037	0.0042	$\Omega$
		$V_{GS} = 10 \text{ V}, I_D = 40 \text{ A}$		0.0042	0.0047	$\Omega$
		$V_{GS} = 4.5 \text{ V}, I_D = 40 \text{ A}$ SMD version		0.0055	0.007	$\Omega$
		$V_{GS} = 4.5 \text{ V}, I_D = 40 \text{ A}$		0.006	0.0075	$\Omega$

**Table 5. Dynamic**

Symbol	Parameter	Test conditions	Min	Typ.	Max.	Unit
$C_{iss}$	Input capacitance			2200		pF
$C_{oss}$	Output capacitance	$V_{DS} = 25 \text{ V}, f=1 \text{ MHz}$ , $V_{GS} = 0$	-	400	-	pF
$C_{rss}$	Reverse transfer capacitance			280		pF
$Q_g$	Total gate charge	$V_{DD} = 15 \text{ V}, I_D = 80 \text{ A}$		20		nC
$Q_{gs}$	Gate-source charge	$V_{GS} = 4.5 \text{ V}$	-	8.2	-	nC
$Q_{gd}$	Gate-drain charge	<i>Figure 13</i>		7.5		nC
$Q_{gs1}$	Pre $V_{th}$ gate-to-source charge	$V_{DD} = 15 \text{ V}, I_D = 80 \text{ A}$		3.4		nC
$Q_{gs2}$	Post $V_{th}$ gate-to-source charge	<i>Figure 18</i>	-	6.2		nC
$R_G$	Gate input resistance	$f = 1 \text{ MHz}$ gate bias Bias = 0 test signal level = 20 mV open drain	-	1	-	$\Omega$

**Table 6. Switching on/off (inductive load)**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ $t_r$	Turn-on delay time Rise time	$V_{DD} = 15 \text{ V}$ , $I_D = 40 \text{ A}$ , $R_G = 4.7 \Omega$ , $V_{GS} = 5 \text{ V}$ <i>Figure 12</i>	-	19 91	-	ns ns
$t_{d(off)}$ $t_f$	Turn-off delay time Fall time	$V_{DD} = 15 \text{ V}$ , $I_D = 40 \text{ A}$ , $R_G = 4.7 \Omega$ , $V_{GS} = 5 \text{ V}$ <i>Figure 12</i>	-	24.5 23.4	-	ns ns

**Table 7. Source drain diode**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{SD}$ $I_{SDM}^{(1)}$	Source-drain current Source-drain current (pulsed)		-		80 320	A A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 40 \text{ A}$ , $V_{GS} = 0$	-		1.1	V
$t_{rr}$ $Q_{rr}$ $I_{RRM}$	Reverse recovery time Reverse recovery charge Reverse recovery current	$I_{SD} = 80 \text{ A}$ , $dI/dt = 100 \text{ A}/\mu\text{s}$ , $V_{DD} = 24 \text{ V}$ <i>Figure 14</i>	-	28.6 22.8 1.6		ns nC A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300  $\mu\text{s}$ , duty cycle 1.5%

## 2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

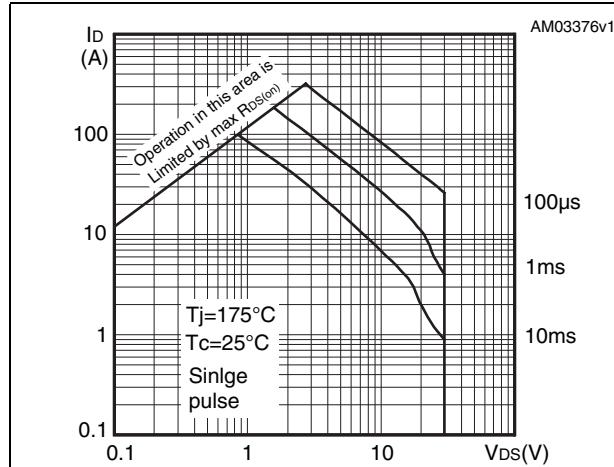


Figure 3. Thermal impedance

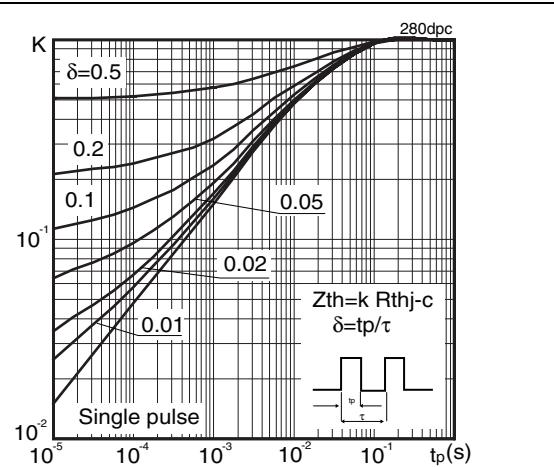


Figure 4. Output characteristics

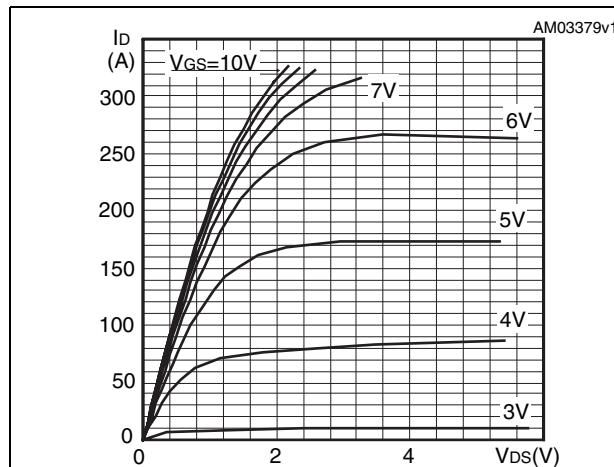


Figure 5. Transfer characteristics

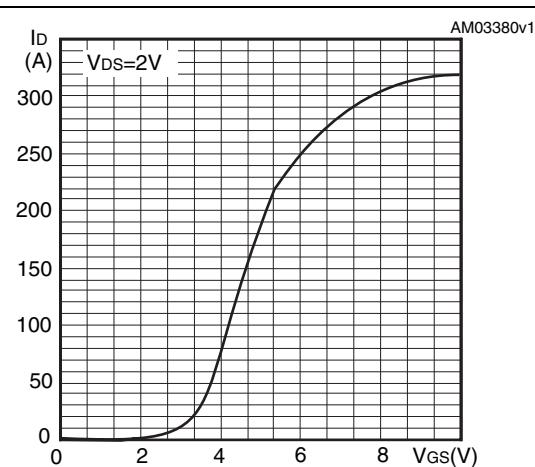
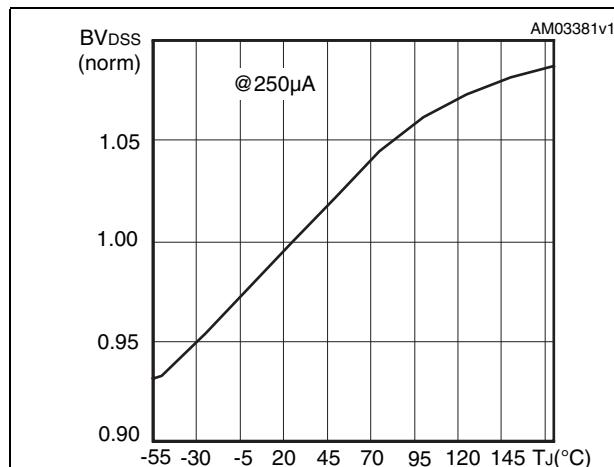
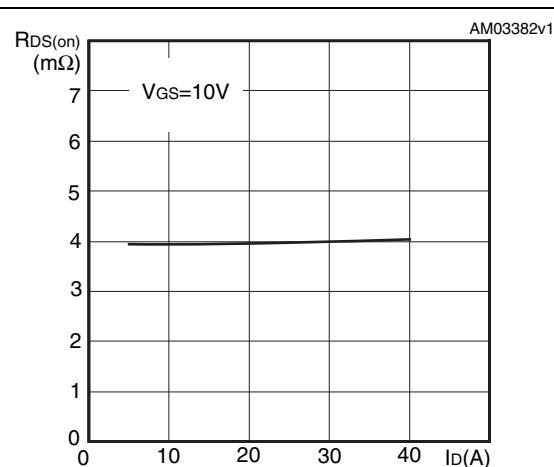
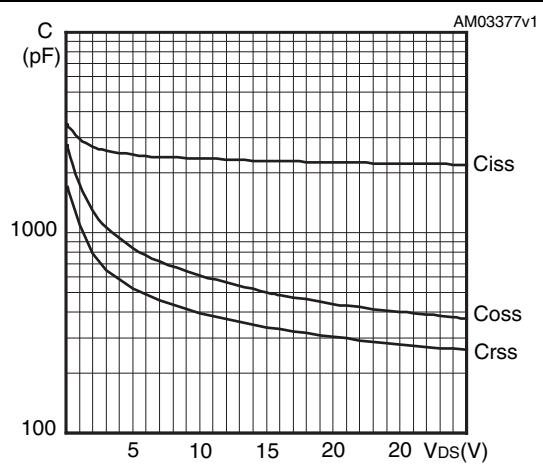
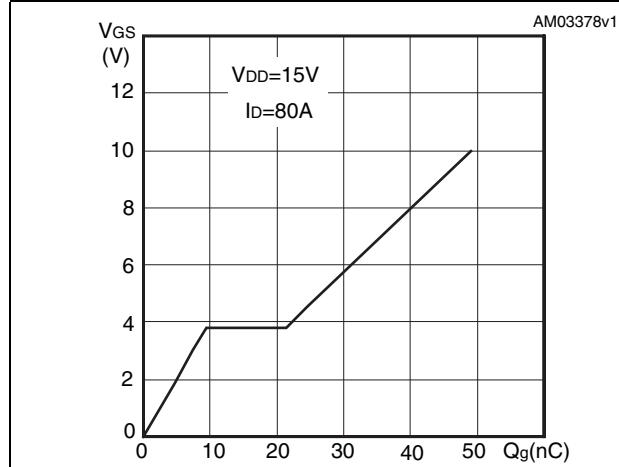
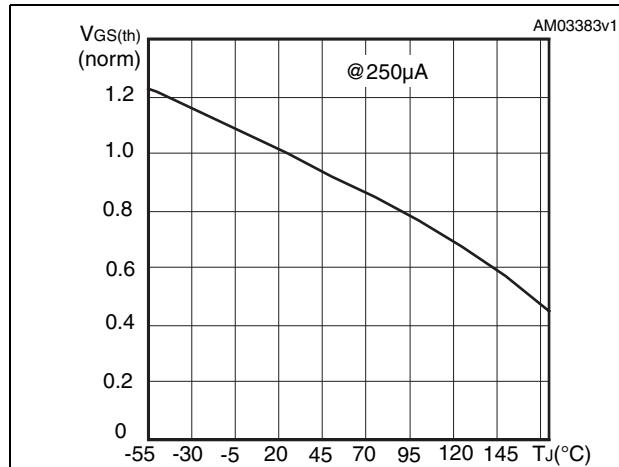
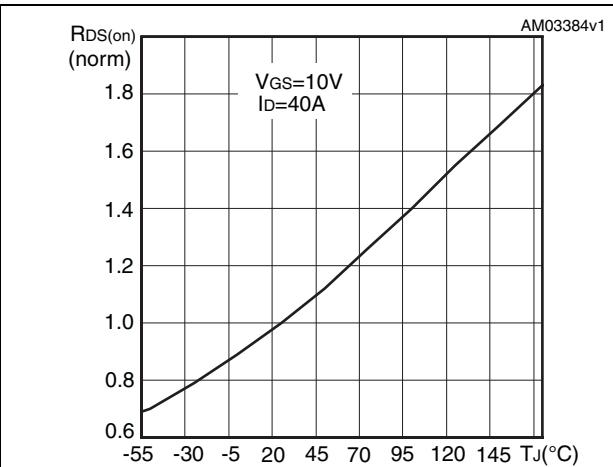
Figure 6. Normalized  $BV_{DSS}$  vs temperature

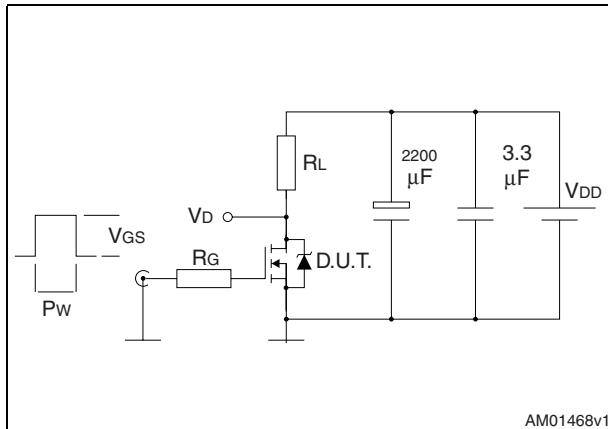
Figure 7. Static drain source on resistance



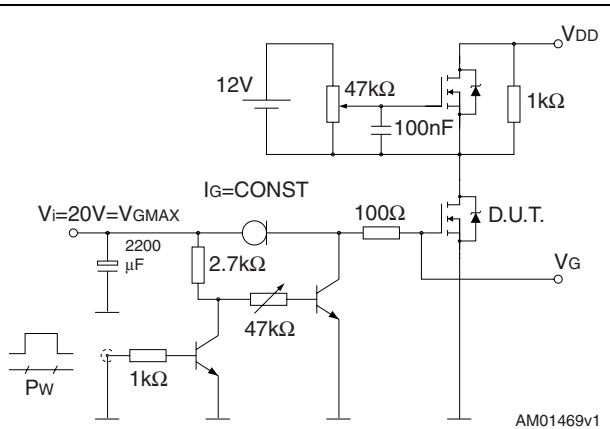
**Figure 8. Gate charge vs gate-source voltage****Figure 10. Normalized gate threshold voltage vs temperature****Figure 11. Normalized on resistance vs temperature**

### 3 Test circuits

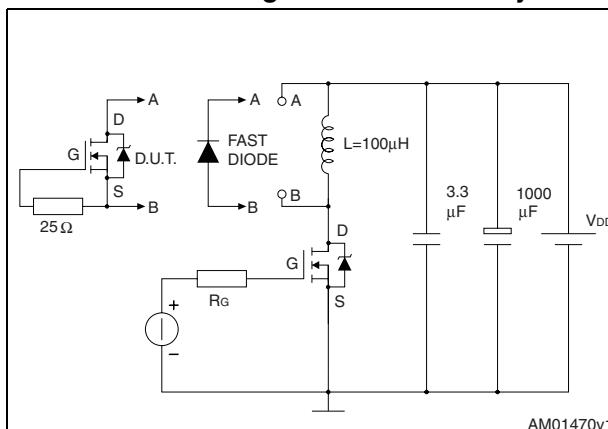
**Figure 12. Switching times test circuit for resistive load**



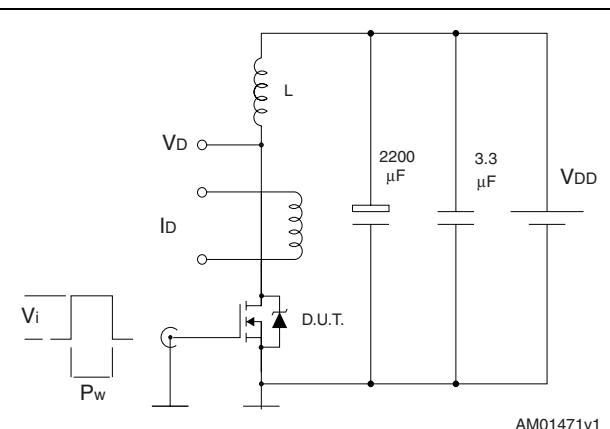
**Figure 13. Gate charge test circuit**



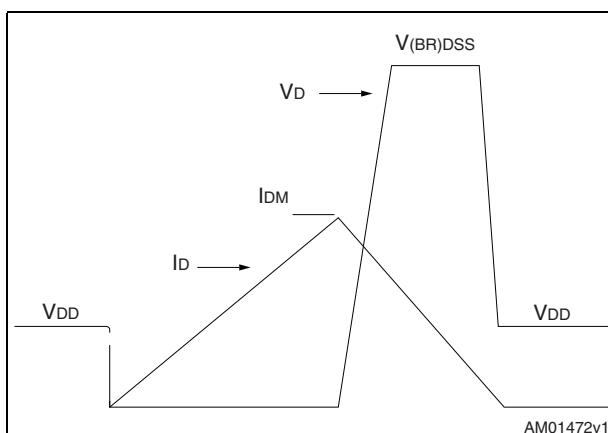
**Figure 14. Test circuit for inductive load switching and diode recovery times**



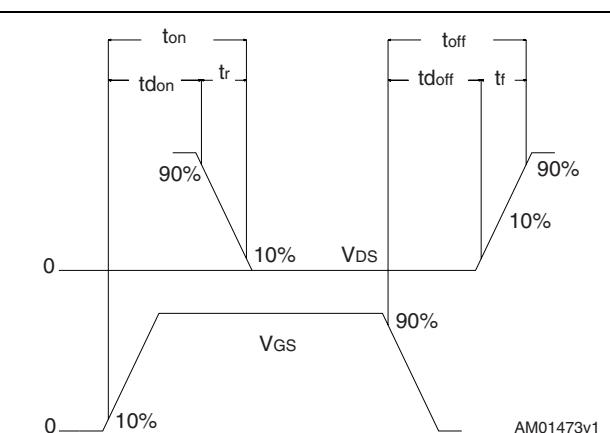
**Figure 15. Unclamped inductive load test circuit**

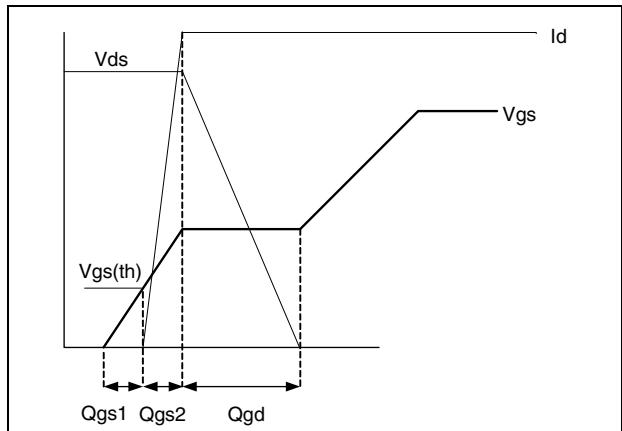


**Figure 16. Unclamped inductive waveform**



**Figure 17. Switching time waveform**



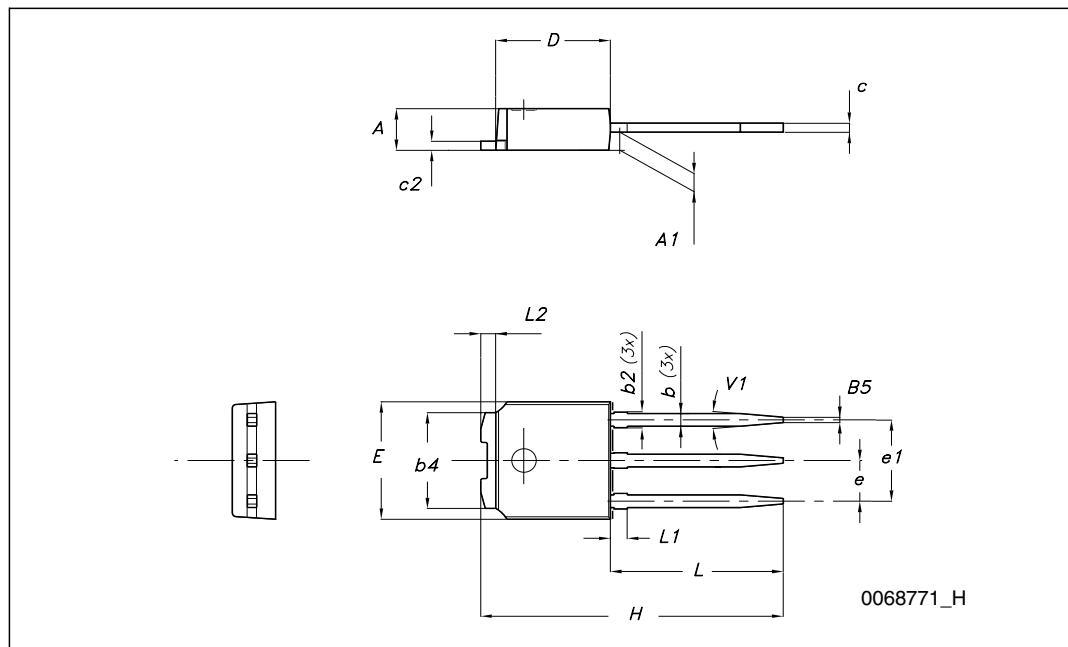
**Figure 18. Gate charge waveform**

## 4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com).  
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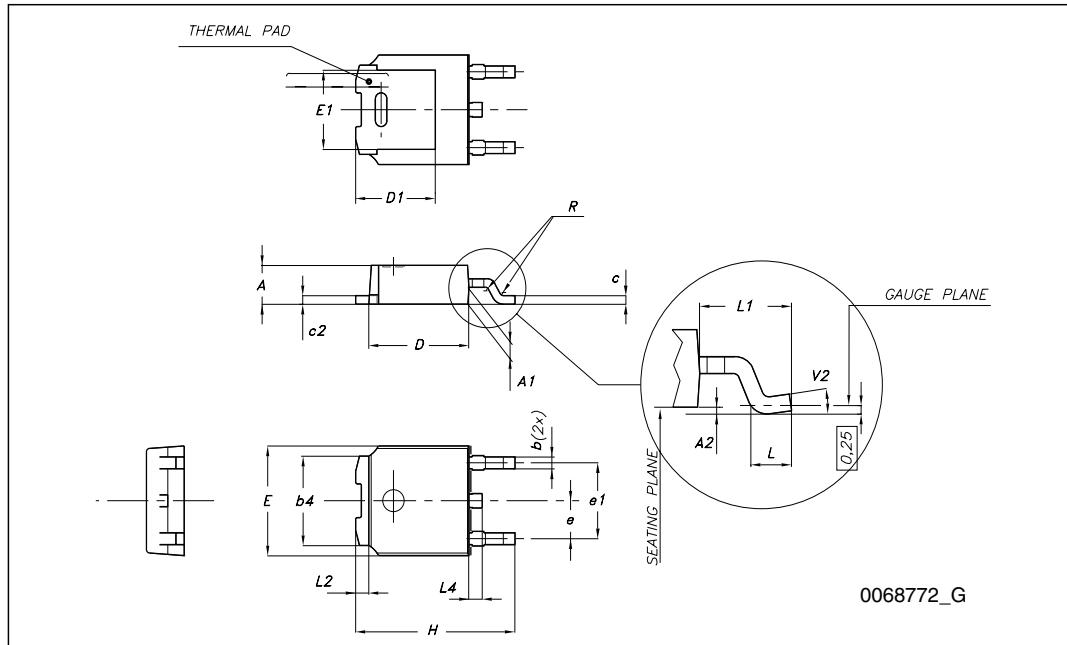
**TO-251 (IPAK) mechanical data**

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
b	0.64		0.90
b2			0.95
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
E	6.40		6.60
e		2.28	
e1	4.40		4.60
H		16.10	
L	9.00		9.40
(L1)	0.80		1.20
L2		0.80	
V1		10°	



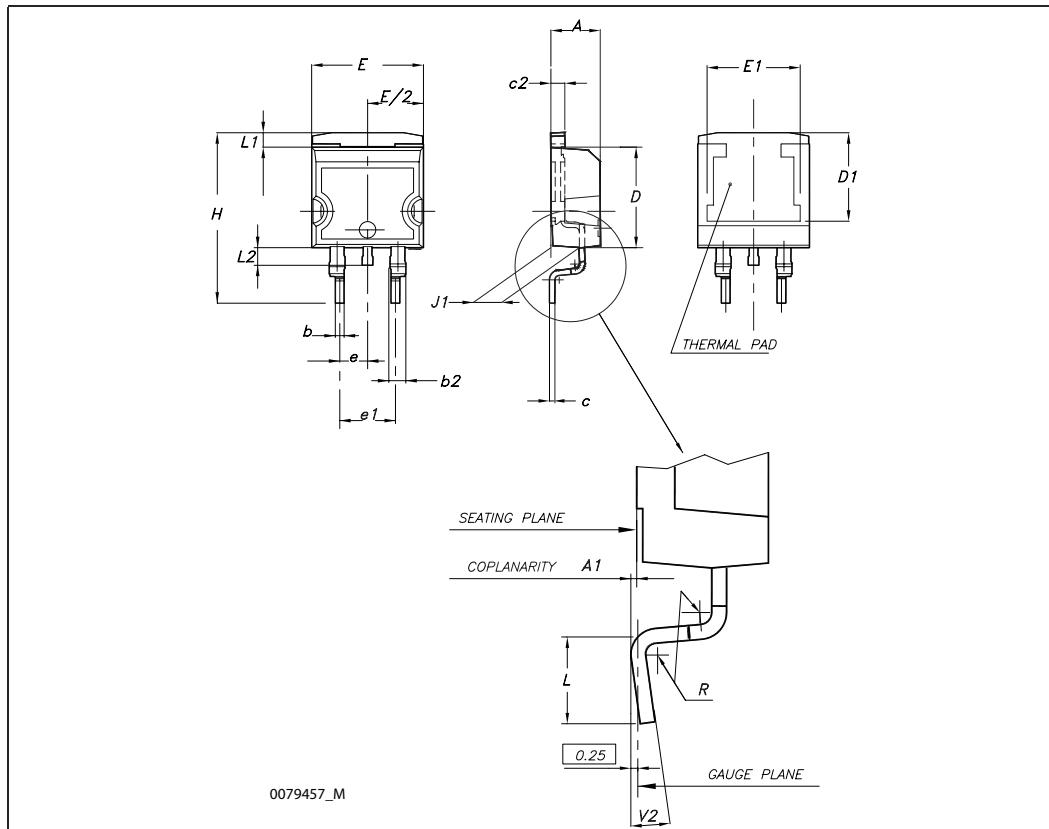
## TO-252 (DPAK) mechanical data

DIM.	mm.		
	min.	typ	max.
A	2.20		2.40
A1	0.90		1.10
A2	0.03		0.23
b	0.64		0.90
b4	5.20		5.40
c	0.45		0.60
c2	0.48		0.60
D	6.00		6.20
D1		5.10	
E	6.40		6.60
E1		4.70	
e		2.28	
e1	4.40		4.60
H	9.35		10.10
L	1		
L1		2.80	
L2		0.80	
L4	0.60		1
R		0.20	
V2	0°		8°



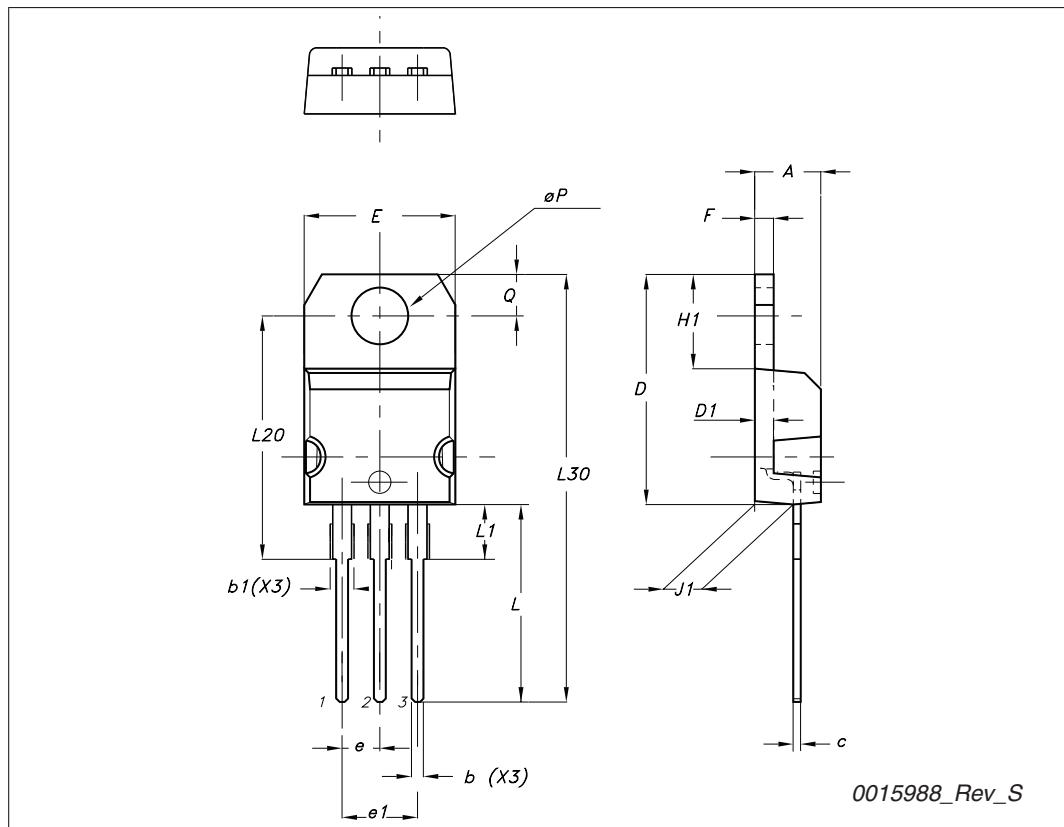
D<sup>2</sup>PAK (TO-263) mechanical data

Dim	mm			inch		
	Min	Typ	Max	Min	Typ	Max
A	4.40		4.60	0.173		0.181
A1	0.03		0.23	0.001		0.009
b	0.70		0.93	0.027		0.037
b2	1.14		1.70	0.045		0.067
c	0.45		0.60	0.017		0.024
c2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1	7.50			0.295		
E	10		10.40	0.394		0.409
E1	8.50			0.334		
e		2.54			0.1	
e1	4.88		5.28	0.192		0.208
H	15		15.85	0.590		0.624
J1	2.49		2.69	0.099		0.106
L	2.29		2.79	0.090		0.110
L1	1.27		1.40	0.05		0.055
L2	1.30		1.75	0.051		0.069
R		0.4			0.016	
V2	0°		8°	0°		8°



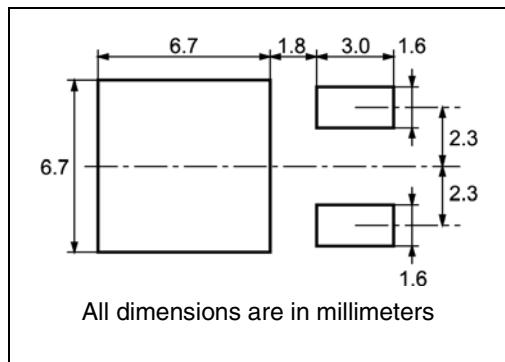
## TO-220 type A mechanical data

Dim	mm		
	Min	Typ	Max
A	4.40		4.60
b	0.61		0.88
b1	1.14		1.70
c	0.48		0.70
D	15.25		15.75
D1		1.27	
E	10		10.40
e	2.40		2.70
e1	4.95		5.15
F	1.23		1.32
H1	6.20		6.60
J1	2.40		2.72
L	13		14
L1	3.50		3.93
L20		16.40	
L30		28.90	
$\emptyset P$	3.75		3.85
Q	2.65		2.95



## 5 Packaging mechanical data

### DPAK FOOTPRINT



### TAPE AND REEL SHIPMENT

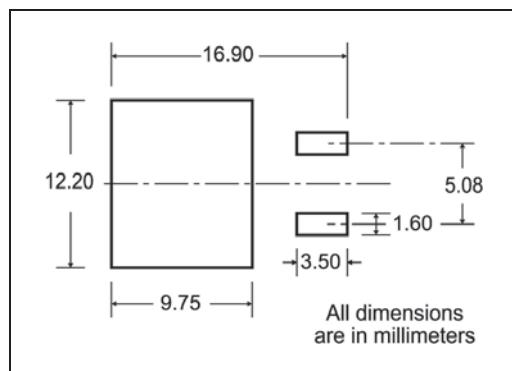
REEL MECHANICAL DATA				
DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A		330		12.992
B	1.5		0.059	
C	12.8	13.2	0.504	0.520
D	20.2		0.795	
G	16.4	18.4	0.645	0.724
N	50		1.968	
T		22.4		0.881

BASE QTY		BULK QTY	
2500		2500	

DIM.	mm		inch	
	MIN.	MAX.	MIN.	MAX.
A0	6.8	7	0.267	0.275
B0	10.4	10.6	0.409	0.417
B1		12.1		0.476
D	1.5	1.6	0.059	0.063
D1	1.5		0.059	
E	1.65	1.85	0.065	0.073
F	7.4	7.6	0.291	0.299
K0	2.55	2.75	0.100	0.108
P0	3.9	4.1	0.153	0.161
P1	7.9	8.1	0.311	0.319
P2	1.9	2.1	0.075	0.082
R	40		1.574	
W	15.7	16.3	0.618	0.641

D<sup>2</sup>PAK FOOTPRINT

## TAPE AND REEL SHIPMENT

REEL MECHANICAL DATA			
DIM.	mm	inch	
	MIN.	MAX.	
A		330	12.992
B	1.5		0.059
C	12.8	13.2	0.504
D	20.2		0.795
G	24.4	26.4	0.960
N	100		3.937
T		30.4	1.197

BASE QTY	BULK QTY
1000	1000

TAPE MECHANICAL DATA

DIM.	mm	inch		
	MIN.	MAX.	MIN.	MAX.
A0	10.5	10.7	0.413	0.421
B0	15.7	15.9	0.618	0.626
D	1.5	1.6	0.059	0.063
D1	1.59	1.61	0.062	0.063
E	1.65	1.85	0.065	0.073
F	11.4	11.6	0.449	0.456
K0	4.8	5.0	0.189	0.197
P0	3.9	4.1	0.153	0.161
P1	11.9	12.1	0.468	0.476
P2	1.9	2.1	0.075	0.082
R	50		1.574	
T	0.25	0.35	0.0098	0.0137
W	23.7	24.3	0.933	0.956

10 pitches cumulative tolerance on tape + / - 0.2 mm

Center line of cavity

User Direction of Feed

TRL

FEED DIRECTION →

Bending radius R min.

## 6 Revision history

**Table 8. Document revision history**

Date	Revision	Changes
01-Dec-2008	1	First release
20-May-2009	2	<ul style="list-style-type: none"><li>– Document status promoted from preliminary data to datasheet.</li><li>– Added new package, mechanical data: D<sup>2</sup>PAK</li></ul>
10-Nov-2009	3	Added new device in TO-220

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[DMN3404LQ-7](#) [NTE6400](#) [SQJ402EP-T1-GE3](#) [2SK2614\(TE16L1,Q\)](#) [2N7002KW-FAI](#) [DMN1017UCP3-7](#) [EFC2J004NUZTDG](#) [ECH8691-](#)  
[TL-W](#) [FCAB21350L1](#) [P85W28HP2F-7071](#) [DMN1053UCP4-7](#) [NTE221](#) [NTE2384](#) [NTE2903](#) [NTE2941](#) [NTE2945](#) [NTE2946](#) [NTE2960](#)  
[NTE2967](#) [NTE2969](#) [NTE2976](#) [NTE455](#) [NTE6400A](#) [NTE2910](#) [NTE2916](#) [NTE2956](#) [NTE2911](#) [DMN2080UCB4-7](#) [TK10A80W,S4X\(S](#)  
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